

SANYO	No.4558	2SC4851
		NPN Epitaxial Planar Silicon Transistor

Muting Circuits

Features

- Very small-sized package permitting 2SC4851-applied sets to be made smaller and slimer.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.

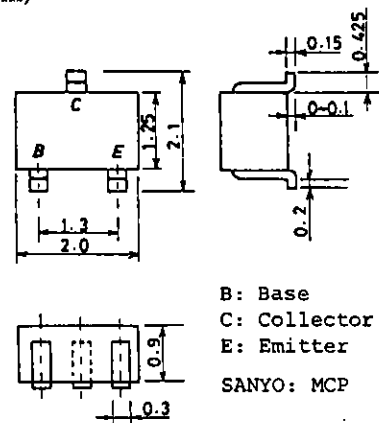
Absolute Maximum Ratings at Ta = 25°C

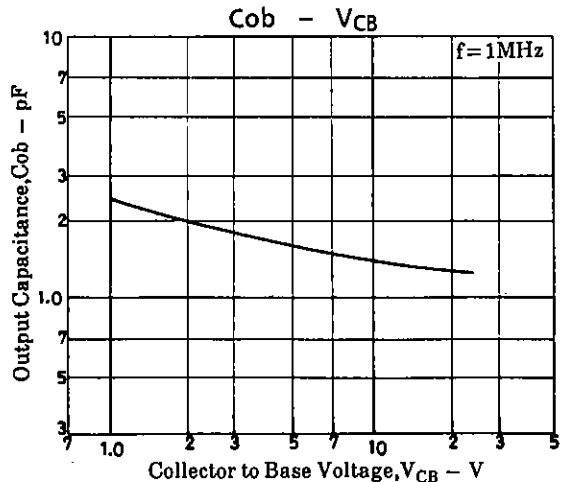
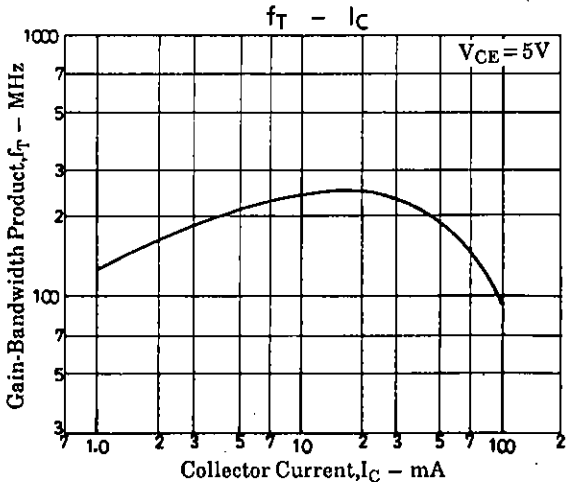
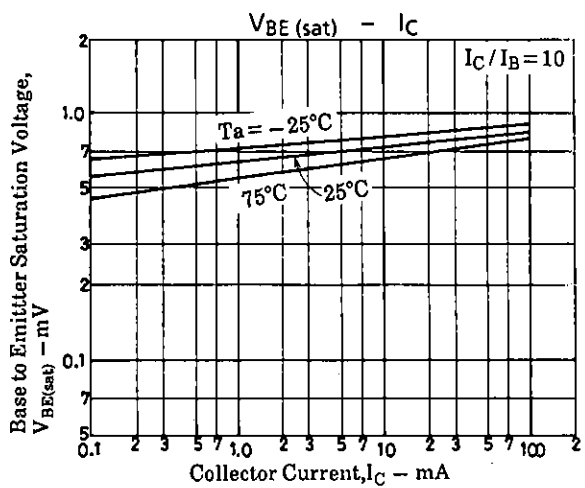
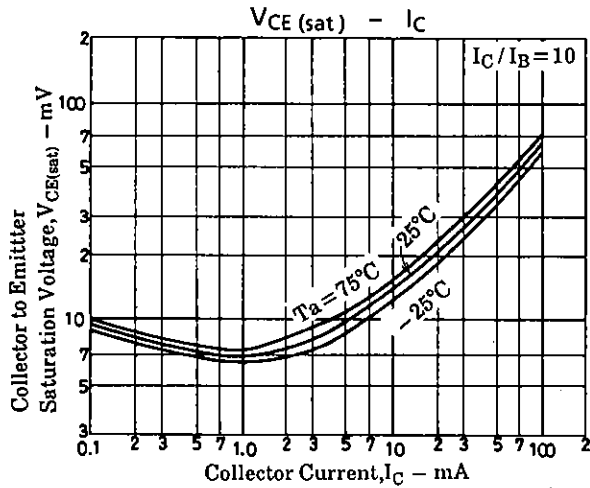
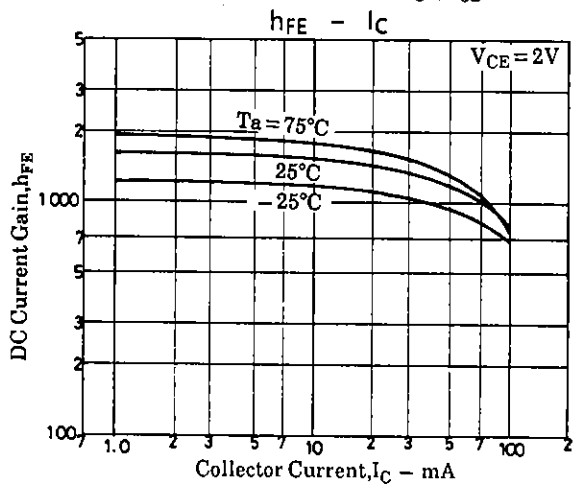
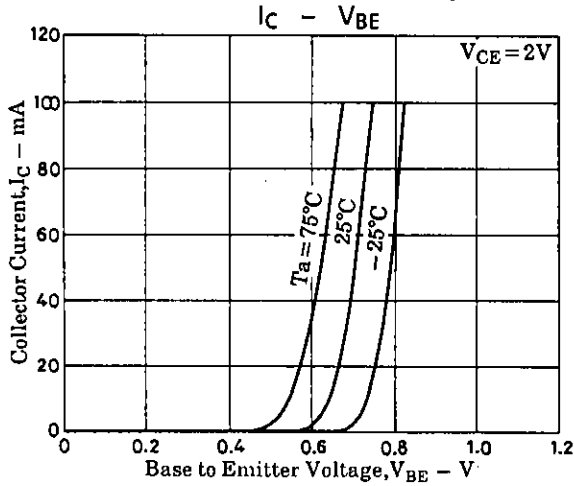
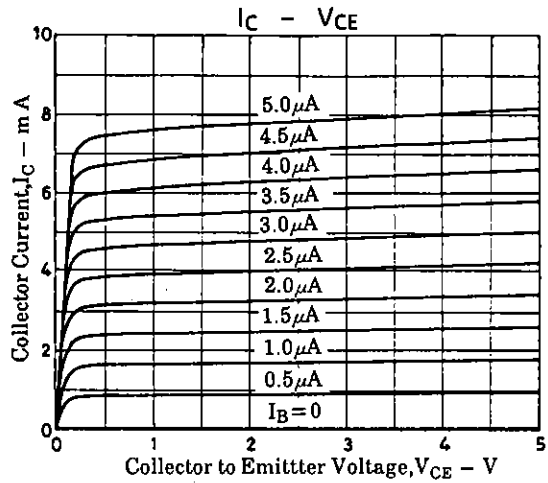
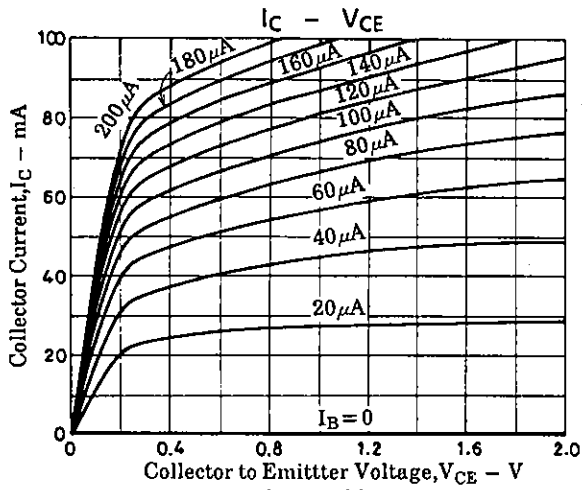
			unit
Collector to Base Voltage	V _{CB0}	25	V
Collector to Emitter Voltage	V _{CEO}	15	V
Emitter to Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA
Collector Current (Pulse)	I _{CP}	200	mA
Base Current	I _B	20	mA
Collector Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	- 55 to + 150	°C

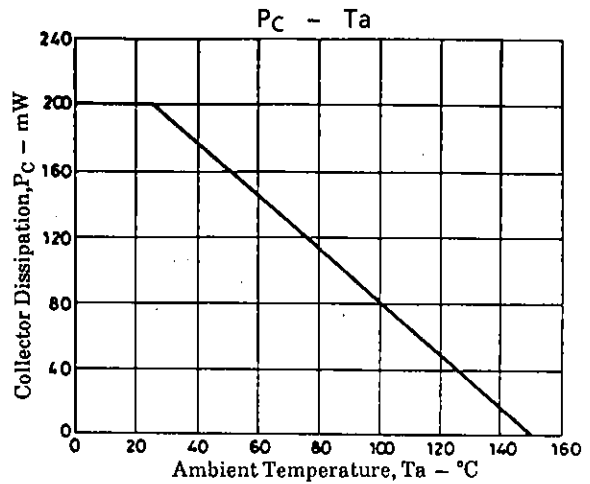
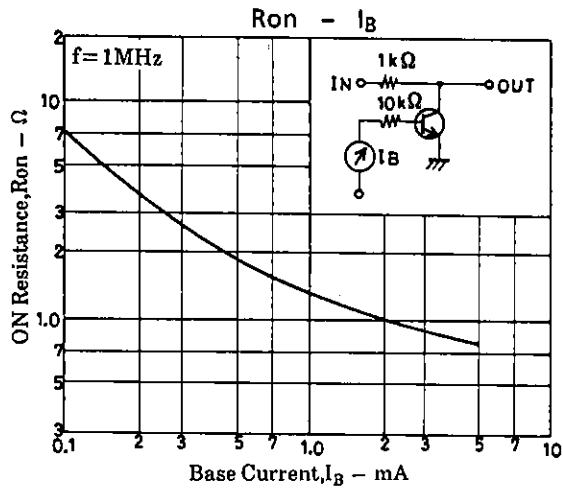
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 15V, I _E = 0			0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 4V, I _C = 0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C = 5mA	800		3200	
Gain-Bandwidth Product	f _T	V _{CE} = 5V, I _C = 10mA		240		MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, f = 1MHz		1.4		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA		14	30	mV
B-E Saturation Voltage	V _{BE(sat)}	I _C = 10mA, I _B = 1mA		0.74	1.1	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	25			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	15			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5			V
ON Resistance	R _{on}	I _B = 3mA, f = 1MHz		0.9		Ω

Marking: YT

Package Dimensions 2059
(unit: mm)





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